

REMARKS/ARGUMENTS

The present amendment is in response to the Office Action mailed October 17, 2003, in which Claims 6, 8 through 10 and 16 through 20 were rejected. Applicant has thoroughly reviewed the outstanding Office Action including the Examiner's remarks and the reference cited therein. The following remarks are believed to be fully responsive to the Office Action and are believed to render all claims at issue patentably distinguishable over the cited references.

No claim is amended herein. No claim is cancelled. No claim is added. Accordingly, Claims 6, 8 through 10 and 16 through 20 remain pending.

Applicant respectfully requests reconsideration in light of the above amendments and the following remarks.

CLAIM REJECTIONS - 35 U.S.C. SECTION 103 (a)

With respect to Paragraphs 1 and 2 of the Office Action, the Examiner rejected Claims 6, 8 through 10 and 16 through 20 under 35 U.S.C. Section 103(a) as being unpatentable over U.S. Patent No. 6,538,270 B1 to Randolph et al. (hereinafter referred to as "Randolph et al.") in view of U.S. Patent No. 5,976,937 to Rodder et al. (hereinafter referred to as "Rodder et al.").

Applicant respectfully traverses this rejection.

Applicant respectfully requests the reconsideration from the examiner and the continued examination in the application, because Claims 6, 8 through 10, and 16 through 20 are not disclosed by Randolph et al. in view of Rodder et

al. The claimed invention provides a method for forming a nitride read only memory with indium ions to form the pocket dopant region for avoiding the defects of boron ions, which is easy to diffuse (page 5, lines 25-26, Claim 6 and 16). The claimed invention can reduce the lateral distribution of pocket dopant with boron ions because the indium ions are difficult to diffuse (page 6, lines 3-6, Claim 6 and 16).

Because Rodder et al. accurately discredit Randolph et al., the citations conflict. As disclosed by Rodder et al., the source pocket 70 is localized and bound an inner perimeter 74 of the localized source extension 52. The drain pocket 72 is localized and bound by an inner perimeter 76 of the localized drain extension 54 (col. 5, lines 46-49 and FIG. 1C). However, as disclosed by Randolph et al., the junction depth of buried bit-line regions 224 is greater than the junction depth of pocket regions 218, 220 (col. 3, lines 59-62 and FIG. 4). The pocket disclosed by Rodder et al. is bound the source extension 52 and the drain extension 54. The pocket disclosed by Rodder et al. cannot be bound the bit-line regions. If the two citations are combined, the pocket that is not bound by the bit-line regions disclosed by Randolph et al. has to be bound by the bit-line regions according to Rodder et al. The structures disclosed by Rodder et al., i.e. the pockets 70 and 72, discredit the structures disclosed by Randolph et al., i.e. the pockets 70 and 72. The citations disclosed by Rodder et al. and Randolph et al. cannot be combined. Hence, Applicant respectfully submits that the claimed invention is patentable over U.S. Patent No. 6,538,270 B1 in view of U.S. Patent No. 5,976,937.

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Furthermore, neither Randolph et al. nor Rodder et al. teach that boron ions for forming pocket dopant regions are easy to diffuse and indium ions for forming pocket dopant regions are difficult to diffuse. Each of them does not concern or mention the problem on which Applicant is focused. Thus one of ordinary skill in the art cannot obtain the claimed invention according to a citation concerns nothing about how to overcome the diffused problem of the pocket dopant regions formed by boron ions. Thus the claimed invention is believed to be patentable over the prior art.

Reconsideration and withdrawal of the rejections under 35 U.S.C. Section 103 are respectfully requested.

CONCLUSION

In light of the above remarks, Applicant respectfully submits that all pending claims as currently presented are in condition for allowance. If, for any reason, the Examiner disagrees, please call the undersigned attorney at 248-433-7552 in an effort to resolve any matter still outstanding before issuing another action. The undersigned attorney is confident that any issue which might remain can readily be worked out by telephone.

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Applicant respectfully requests that a timely Notice of Allowance be issued in this case.

Respectfully submitted,



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